

SSCN5551GS7

High Frequency High Gain NPN Power BJT

> Features

VCB	VCE	VEB	IC
180V	160V	6V	600mA

Pin configuration

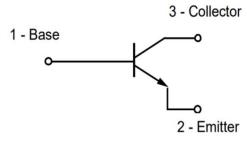


> Description

This device is designed for general-purpose high-voltage amplifiers and gas discharge display drivers. It is Ideal for medium power amplification and switching.

> Applications

- General-purpose high-voltage amplifiers
- Gas discharge display drivers
- Medium power amplification and switching



Circuit Diagram

> Ordering Information

Device	Package	Shipping
SSCN5551GS7	SOT-323	3000/Reel





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> Absolute Maximum Ratings($T_A=25^{\circ}C$ unless otherwise noted)

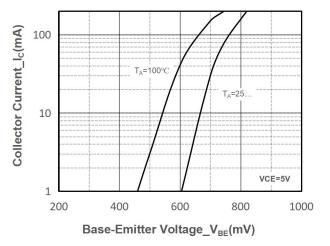
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	180	V
Collector- Emitter Voltage	VCEO	160	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current-Continuous	lc	600	mA
Collector Power Dissipation	Pc	200	mW
Thermal Resistance From Junction To Ambient	Roja	625	°C/W
Junction Temperature	TJ	-55 to 150	°C
Storage Temperature	Тѕтс	-55 to 150	°C

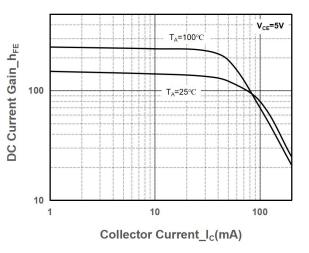
➢ Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =0.1mA, I _E =0	180			V
Collector-emitter Breakdown Voltage	BV _{CEO}	I _C =1mA, I _B =0	160			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E =0.1mA, I _C =0	6			V
Collector Cutoff Current	I _{СВО}	V _{CB} =120V, I _E =0			0.05	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =4V, I _C =0			0.05	μA
	h _{FE1}	V _{CE} =5V, I _C =1mA	80			
DC Current Gain	h _{FE2}	V _{CE} =5V, I _C =10mA	100		300	
	h _{FE3}	V _{CE} =5V, I _C =50mA	30			
Collector Emitter Seturation Voltage	V _{CE (sat)1}	I _C =10mA, I _B =1mA			0.15	V
Collector-Emitter Saturation Voltage	V _{CE (sat)2}	Ic=50mA, I _B =5mA			0.2	V
Read Emitter Seturation Voltage	V _{BE (sat)1}	Ic=10mA, I _B =1mA			1.0	V
Base-Emitter Saturation Voltage	V _{BE (sat)2}	I _C =50mA, I _B =5mA			1.0	V
Output Consiltance	Cob	VCB=10V, IE=0,			6	pF
Output Capacitance		f=1MHz				
Transition fragmanay	fT	V _{CE} =10V, I _C =10mA	100	0	300	MHz
Transition frequency		f=100MHz	100			

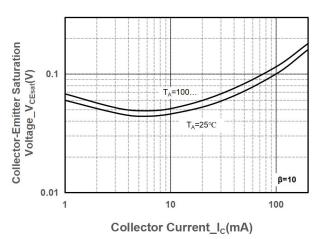


> Typical Performance Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

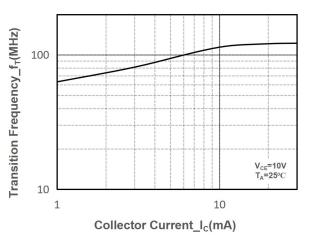




DC Current Gain vs. Collector Current



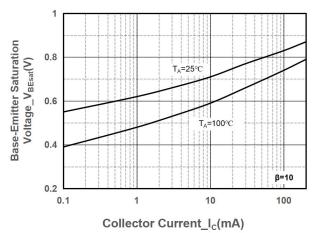
V_{CE(sat)} vs. Collector Current



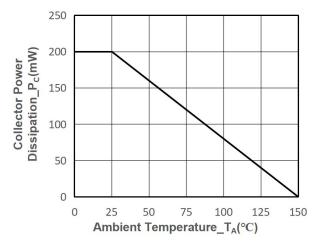


Transition Frequency vs. Collector Current

Collector Current vs. Base-Emitter Voltage





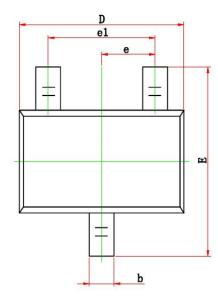


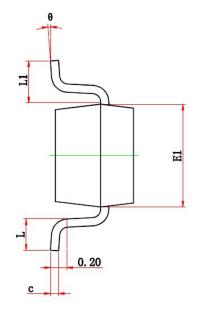


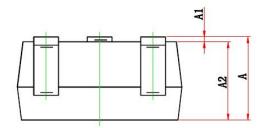
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Package Information









Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	2.150	2.450	0.085	0.096	
E1	1.150	1.350	0.045	0.053	
e	0.650 TYP.		0.026 TYP.		
e1	1.200	1.400	0.047	0.055	
L.	0.260	0.460	0.010	0.018	
L1	0.525 REF.		0.021 REF.		
θ	0°	8°	0°	8°	



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